Low-power dual function gate Rev. 6 — 21 October 2010

Product data sheet

#### **General description** 1.

The 74AUP1G885 provides two functions in one device. The output state of the outputs (1Y, 2Y) is determined by the inputs (A, B and C). The output 1Y provides the Boolean function:  $1Y = A \times C$ . The output 2Y provides the Boolean function:  $2Y = A \times B + A \times C$ .

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

#### 2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



# 3. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G885DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP1G885GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 $\times$ 1.95 $\times$ 0.5 mm	SOT833-1
74AUP1G885GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089
74AUP1G885GD	–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2
74AUP1G885GM	–40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-1
74AUP1G885GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116
74AUP1G885GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

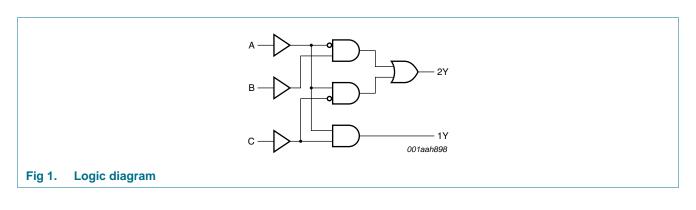
## 4. Marking

### Table 2.Marking codes

5	
Type number	Marking code <sup>[1]</sup>
74AUP1G885DC	pS8
74AUP1G885GT	pS8
74AUP1G885GF	58
74AUP1G885GD	pS8
74AUP1G885GM	pS8
74AUP1G885GN	58
74AUP1G885GS	58

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

# 5. Functional diagram

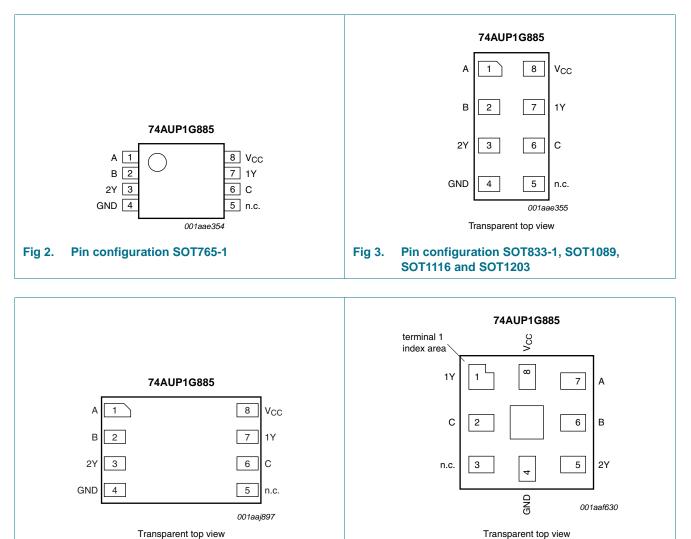


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#### **Pinning information** 6.

## 6.1 Pinning



Transparent top view

Fig 5. Pin configuration SOT902-1

## 6.2 Pin description

Pin configuration SOT996-2

Discute a substitution

Symbol	Pin		Description	
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-1		
A, B, C	1, 2, 6	7, 6, 2	data input	
GND	4	4	ground (0 V)	
n.c.	5	3	not connected	
1Y, 2Y	7, 3	1, 5	data output	
V <sub>CC</sub>	8	8	supply voltage	
74AUP1G885	All information provide	d in this document is subject t	to legal disclaimers	© NXP B.V. 2010. All rights reserved.

Fig 4.

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## 7. Functional description

Table 4.	Function table <sup>[1]</sup>					
Input			Output			
Α	В	C	1Y	2Y		
L	L	L	L	L		
Н	L	L	L	Н		
L	Н	L	L	Н		
Н	Н	L	L	Н		
L	L	Н	L	L		
Н	L	Н	Н	L		
L	Н	Н	L	Н		
Н	Н	Н	Н	L		

[1] H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to $V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P<sub>tot</sub> derates linearly with 8.0 mW/K.

For XSON8, XSON8U and XQFN8U packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

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# 9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	-	200	ns/V

## **10. Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V}$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC}$ = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O}$ = -1.9 mA; $V_{CC}$ = 1.65 V	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu A;$ $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_{O}$ = 1.9 mA; $V_{CC}$ = 1.65 V	-	-	0.31	V
		$I_0$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I <sub>I</sub>	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.2	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μΑ
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC};  I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.5	μΑ
$\Delta I_{CC}$	additional supply current		<u>[1]</u> -	-	40	μΑ
CI	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_{I}$ = GND or $V_{CC}$	-	0.6	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.3	-	pF
T <sub>amb</sub> = -	40 °C to +85 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>ОН</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = -20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7  imes V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	_	_	V

#### Table 7. Static characteristics ... continued

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## **NXP Semiconductors**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.33	V
		$I_{O}$ = 3.1 mA; $V_{CC}$ = 2.3 V	-	-	0.45	V
		$I_{O}$ = 2.7 mA; $V_{CC}$ = 3.0 V	-	-	0.33	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.45	V
I <sub>I</sub>	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	0.9	μA
∆l <sub>CC</sub>	additional supply current		<u>[1]</u> -	-	50	μA
T <sub>amb</sub> = -4	40 °C to +125 °C					
	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75  imes V_{CC}$	; -	-	V
		$V_{CC} = 0.9 V \text{ to } 1.95 V$	$0.70  imes V_{CC}$	; -	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25\times V_{CC}$	V
		$V_{CC} = 0.9 V \text{ to } 1.95 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	-	-	0.9	V
V <sub>он</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = –20 $\mu\text{A};~V_{CC}$ = 0.8 V to 3.6 V	$V_{CC} - 0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O}$ = -1.9 mA; $V_{CC}$ = 1.65 V	1.17	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O}$ = -2.7 mA; $V_{CC}$ = 3.0 V	2.40	-	-	V
		$I_{O}$ = -4.0 mA; $V_{CC}$ = 3.0 V	2.30	-	-	V

#### Static characteristics ... continued Table 7.

## **NXP Semiconductors**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu A;$ $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O}$ = 1.9 mA; $V_{CC}$ = 1.65 V	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O}$ = 2.7 mA; $V_{CC}$ = 3.0 V	-	-	0.36	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.50	V
I <sub>I</sub>	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.75	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	1.4	μΑ
$\Delta I_{CC}$	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> _	-	75	μΑ

### Table 7. Static characteristics ...continued

[1] One input at  $V_{CC}$  – 0.6 V, other inputs at  $V_{CC}$  or GND.

# **11. Dynamic characteristics**

### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 7.

Symbo	Parameter	Conditions		25 °C		-40	0 °C to +1	25 °C	Unit
			Min	Typ[1]	Мах	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5	pF						1		
t <sub>pd</sub>	propagation delay	A, C to 1Y; see Figure 6							
		$V_{CC} = 0.8 V$	-	17.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.1	5.2	9.7	0.9	12.8	14.2	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.2	3.7	5.9	1.0	7.8	8.6	ns
		$V_{CC}$ = 1.65 V to 1.95 V	1.1	3.0	4.8	0.9	6.2	6.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.1	2.4	3.6	1.0	4.1	4.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.1	2.1	3.1	1.0	3.6	4.1	ns
		A, B to 2Y; see Figure 6							
		$V_{CC} = 0.8 V$	-	21.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.7	6.0	12.7	1.4	12.8	14.2	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.7	4.2	7.2	1.4	7.8	8.7	ns
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	1.4	3.3	5.8	1.2	6.5	7.2	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.2	2.6	4.1	1.0	4.7	5.2	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.1	2.3	3.5	0.9	3.8	4.2	ns
C <sub>L</sub> = 10	) pF								
t <sub>pd</sub>	propagation delay	A, C to 1Y; see Figure 6							
		$V_{CC} = 0.8 V$	-	20.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.2	6.1	11.4	1.2	14.6	16.1	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.4	4.3	7.2	1.2	8.7	9.6	ns
		$V_{CC}$ = 1.65 V to 1.95 V	1.4	3.6	5.7	1.3	6.8	7.5	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.4	2.9	4.2	1.2	4.8	5.4	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.4	2.7	3.9	1.3	4.1	4.6	ns
		A, B to 2Y; see Figure 6							
		$V_{CC} = 0.8 V$	-	25.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.8	6.9	14.4	1.7	14.6	16.1	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.9	4.8	8.5	1.5	9.1	10.1	ns
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	1.9	3.9	6.6	1.7	7.2	8.0	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.5	3.1	4.7	1.3	5.4	5.9	ns
		$V_{CC}$ = 3.0 V to 3.6 V	1.4	2.8	4.3	1.3	4.6	5.1	ns

Low-power dual function gate

Symbol	Parameter	Conditions		25 °C		-40	0 °C to +1	25 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)           -         r           17.9         r           10.8         r           6.0         r           5.3         r           11.4         r           9.1         r           6.7         r           7.3         r           7.3         r           23.7         r	_
C <sub>L</sub> = 15 p	ρF								
t <sub>pd</sub>	propagation delay	A, C to 1Y; see Figure 6	<u>2]</u>						
		$V_{CC} = 0.8 V$	-	24.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	1.3	6.9	13.0	1.2	16.2	17.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	1.7	4.9	8.0	1.4	9.7	10.8	ns
		$V_{CC}$ = 1.65 V to 1.95 V	1.5	4.1	6.4	1.4	7.6	8.4	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.7	3.4	5.0	1.6	5.4	6.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.7	3.1	4.4	1.6	4.7	5.3	ns
		A, B to 2Y; see Figure 6	<u>2]</u>						
		$V_{CC} = 0.8 V$	-	28.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.1	7.7	16.0	1.9	16.3	18.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.2	5.4	9.4	2.4	10.3	11.4	ns
		$V_{CC}$ = 1.65 V to 1.95 V	2.0	4.4	7.4	1.8	8.2	9.1	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.8	3.6	5.5	1.6	6.0	6.7	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.7	3.3	4.8	1.5	5.2	5.8	ns
C <sub>L</sub> = 30 p	ρF								
t <sub>pd</sub>	propagation delay	A, C to 1Y; see Figure 6	2]						
		$V_{CC} = 0.8 V$	-	34.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.4	9.2	17.7	2.3	20.9	23.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.5	6.5	10.6	2.5	12.2	13.5	ns
		$V_{CC}$ = 1.65 V to 1.95 V	2.5	5.4	8.5	2.4	9.4	10.4	ns
		$V_{CC}$ = 2.3 V to 2.7 V	2.6	4.5	6.4	2.4	7.0	7.7	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.5	4.2	5.7	2.3	6.6	7.3	ns
		A, B to 2Y; see Figure 6	2]						
		$V_{CC} = 0.8 V$	-	38.9	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.6	10.0	20.5	2.6	21.5	23.7	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V	2.6	6.9	11.9	2.6	13.2	14.5	ns
		$V_{CC}$ = 1.65 V to 1.95 V	2.7	5.7	9.5	2.7	10.5	11.6	ns
		$V_{CC}$ = 2.3 V to 2.7 V	2.5	4.7	6.9	2.5	7.6	8.4	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.4	4.4	6.1	2.4	7.1	7.9	ns

#### Table 8. Dynamic characteristics ... continued

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Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pl	F, 10 pF, 15 pF and	30 pF							
C <sub>PD</sub>	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_1 = \text{GND to } V_{\text{CC}}$ [3][4]							
		$V_{CC} = 0.8 V$	-	2.7	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	2.9	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	-	3.0	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	-	3.1	-	-	-	-	pF
		$V_{CC}$ = 2.3 V to 2.7 V	-	3.5	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	4.1	-	-	-	-	pF

#### Table 8. Dynamic characteristics ... continued

[1] All typical values are measured at nominal  $V_{CC}$ .

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[3] All specified values are the average typical values over all stated loads.

[4]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_0$  = output frequency in MHz;

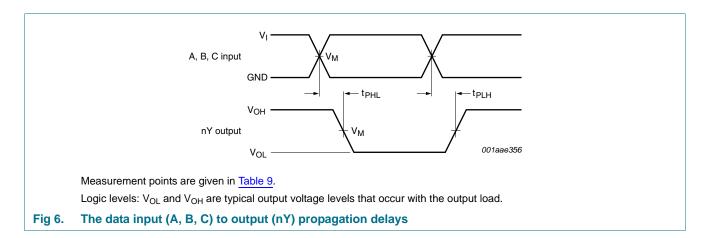
 $C_L$  = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

## 12. Waveforms

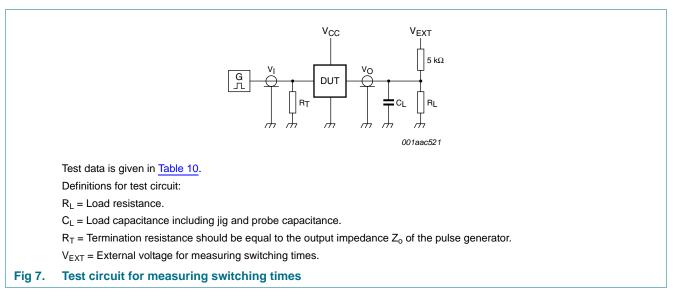


#### Table 9. **Measurement points**

Supply voltage	Output	Input			
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	$t_r = t_f$	
0.8 V to 3.6 V	$0.5  imes V_{CC}$	$0.5  imes V_{CC}$	V <sub>CC</sub>	≤ 3.0 ns	

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### Table 10. Test data

Supply voltage	Load	V <sub>EXT</sub>			
V <sub>cc</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$

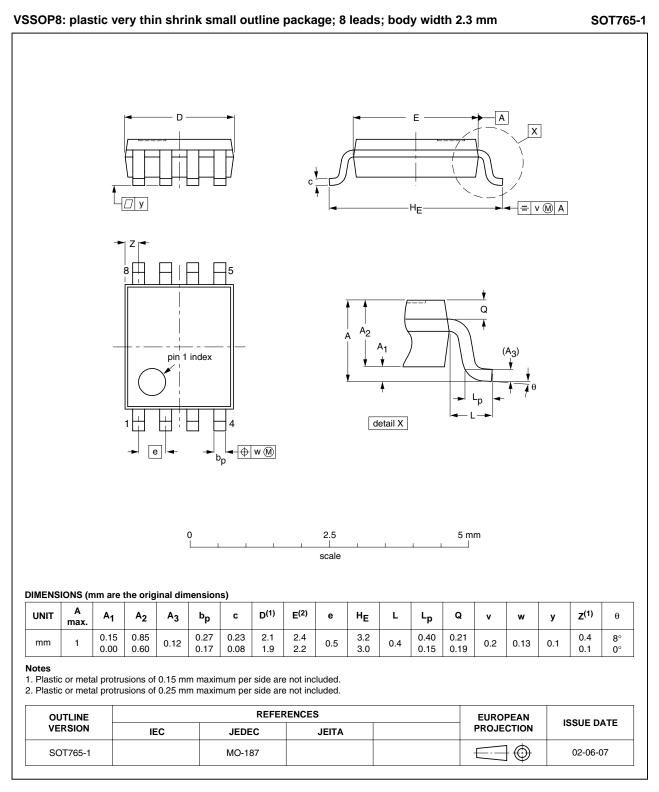
[1] For measuring enable and disable times  $R_L = 5 k\Omega$ .

For measuring propagation delays, set-up and hold times and pulse width  $R_L$  = 1 M $\Omega$ .

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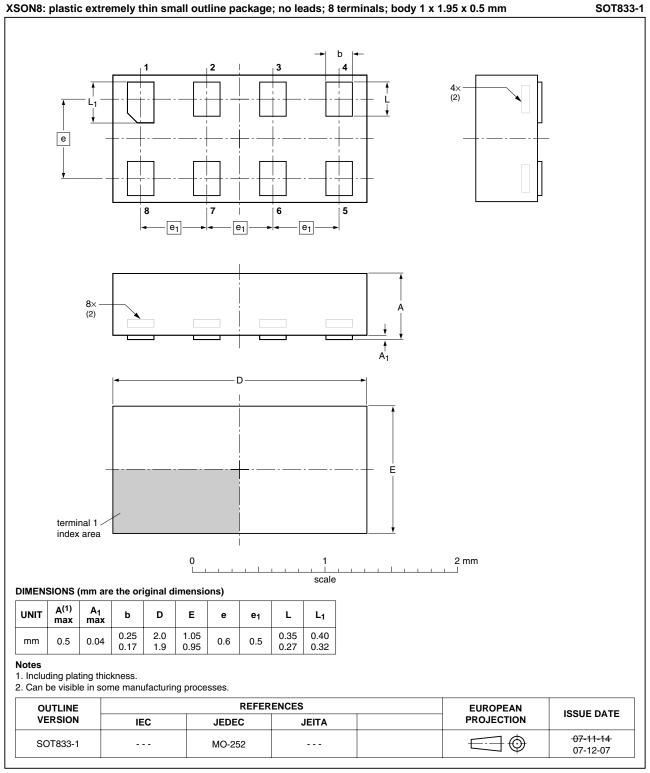
## 13. Package outline



### Fig 8. Package outline SOT765-1 (VSSOP8)

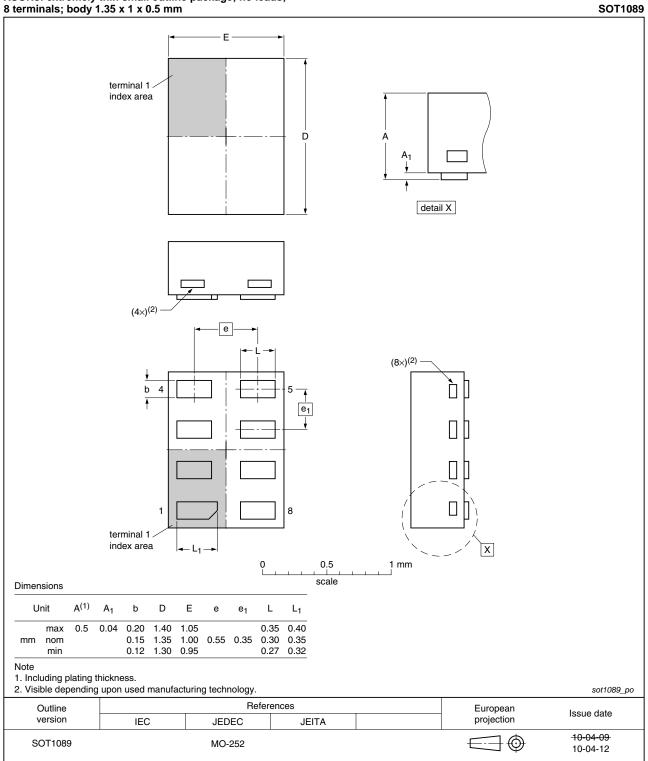
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#### Package outline SOT833-1 (XSON8) Fig 9.

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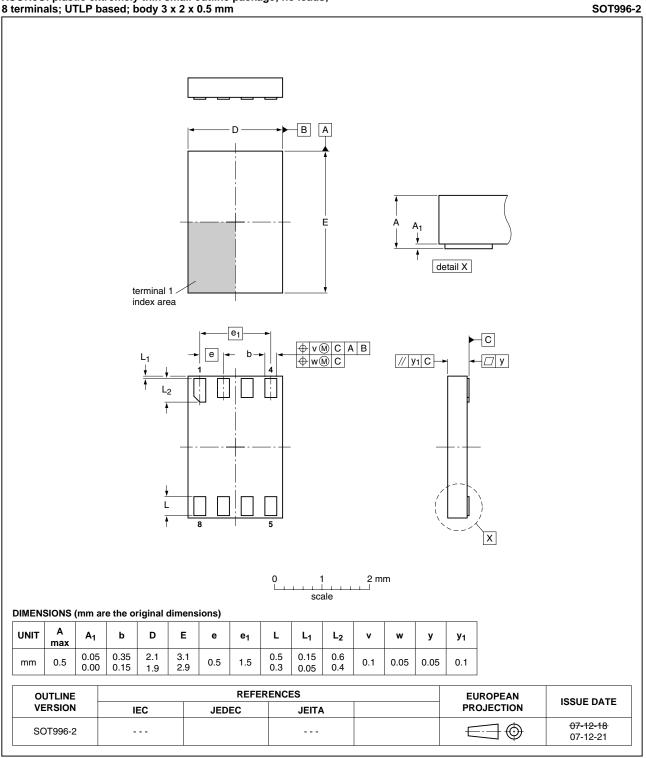


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 10. Package outline SOT1089 (XSON8)

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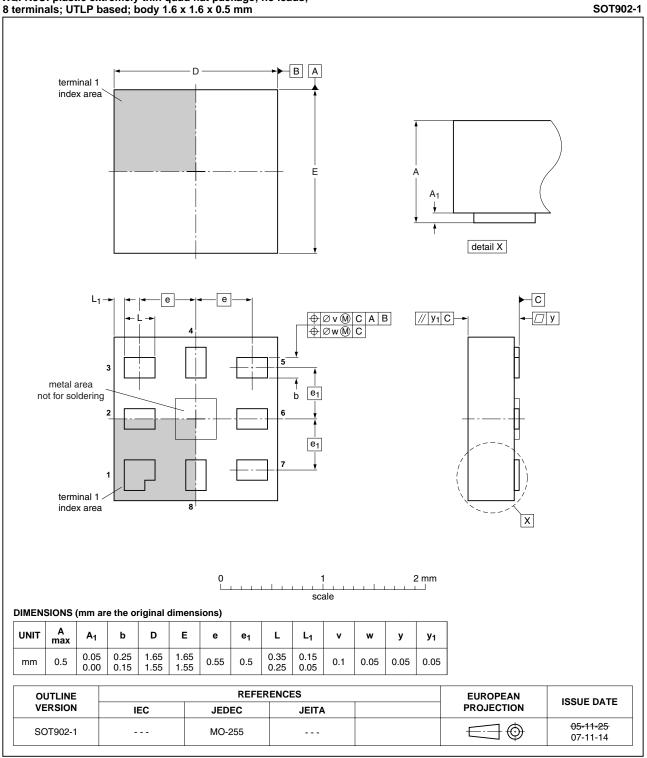


XSON8U: plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 x 2 x 0.5 mm

#### Fig 11. Package outline SOT996-2 (XSON8U)

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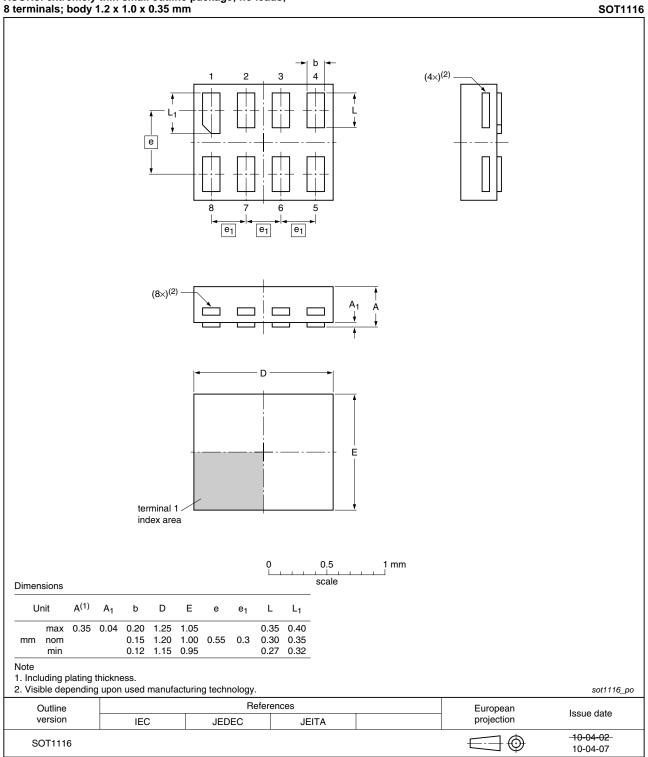




# XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

Fig 12. Package outline SOT902-1 (XQFN8U)

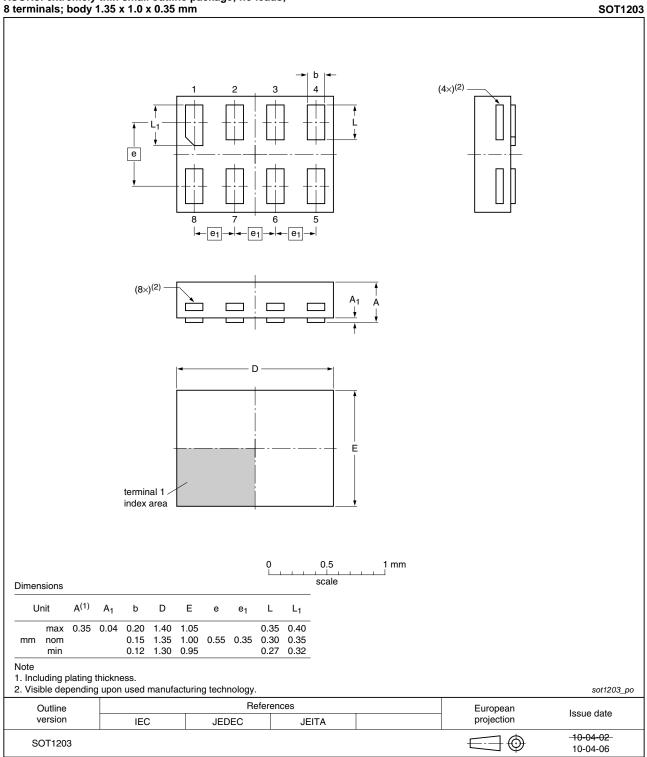
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# XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1116 (XSON8)

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# XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1203 (XSON8)

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## 14. Abbreviations

Acronym	Description	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
НВМ	Human Body Model	
MM	Machine Model	

# **15. Revision history**

Table 12. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G885 v.6	20101021	Product data sheet	-	74AUP1G885 v.5
Modifications:	<ul> <li>Added type r</li> </ul>	number 74AUP1G885GF (SOT	T1089/XSON8 packag	e).
	<ul> <li>Added type r</li> </ul>	number 74AUP1G885GN (SO	T1116/XSON8 packag	e).
	<ul> <li>Added type r</li> </ul>	number 74AUP1G885GS (SO	T1203/XSON8 packag	e).
74AUP1G885 v.5	20090626	Product data sheet	-	74AUP1G885 v.4
74AUP1G885 v.4	20090401	Product data sheet	-	74AUP1G885 v.3
74AUP1G885 v.3	20080328	Product data sheet	-	74AUP1G885 v.2
74AUP1G885 v.2	20070710	Product data sheet	-	74AUP1G885 v.1
74AUP1G885 v.1	20061201	Product data sheet	-	-

## **16. Legal information**

## 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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